

MOSFET – Power, Single P-Channel, SOT-23

-50 V, 10 Ω

BSS84L, BVSS84L, SBSS84L

- SOT-23 Surface Mount Package Saves Board Space
- BV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and **PPAP** Capable
- These Devices are Pb-Free and are RoHS Compliant

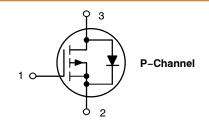
MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DSS}	-50	Vdc
Gate-to-Source Voltage - Continuous	V _{GS}	± 20	Vdc
Drain Current Continuous @ $T_A = 25^{\circ}C$ Pulsed Drain Current $(t_p \le 10 \ \mu s)$	I _D I _{DM}	-130 -520	mA
Total Power Dissipation @ T _A = 25°C	P_{D}	225	mW
Operating and Storage Temperature Range	T _J , T _{stg}	– 55 to 150	°C
Thermal Resistance – Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Thermal Resistance – Junction-to-Ambient (Note 1)	$R_{\theta JA}$	377.2	°C/W
Maximum Lead Temperature for Soldering Purposes, for 10 seconds	T_L	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. And the $R_{\theta JA}$ is determined by the user's board design. The maximum rating presented here is based on mounting the part on JEDEC Standard 51-3/51-7.

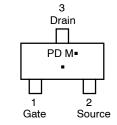
V _{(BR)DSS}	R _{DS(ON)} MAX
-50 V	10 Ω @ -10 V





SOT-23 **CASE 318** STYLE 21

MARKING DIAGRAM & PIN ASSIGNMENT



PD= Specific Device Code

Μ = Date Code

= Pb-Free Package

(*Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
BSS84LT1G, BVSS84LT1G, SBSS84LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
BSS84LT7G	SOT-23 (Pb-Free)	3,500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

С	Symbol	Min	Тур	Max	Unit		
OFF CHARACTERISTICS		•		•			
Drain-to-Source Breakdown Volt ($V_{GS} = 0 \text{ Vdc}, I_D = -250 \mu\text{Adc}$	V _{(BR)DSS}	-50	-	-	Vdc		
Zero Gate Voltage Drain Current	I _{DSS}	- - -	- - -	-0.1 -15 -60	μAdc		
Gate-Body Leakage Current (V _G	I _{GSS}	-	-	±10	nAdc		
ON CHARACTERISTICS (Note 2)						
Gate-Source Threaded Voltage (V _{GS(th)}	-0.9	-	-2.0	Vdc		
Static Drain-to-Source On-Resis	R _{DS(on)}	-	4.7	10	Ω		
Transfer Admittance (V _{DS} = -25 \	y _{fs}	50	-	-	mS		
DYNAMIC CHARACTERISTICS							
Input Capacitance	V _{DS} = 5.0 Vdc	C _{iss}	_	36	-	– pF	
Output Capacitance	V _{DS} = 5.0 Vdc	C _{oss}	_	17	17 –		
Transfer Capacitance	V _{DG} = 5.0 Vdc	C _{rss}	=	6.5	-		
SWITCHING CHARACTERISTIC	S (Note 3)						
Turn-On Delay Time		t _{d(on)}	-	3.6	-	ns	
Rise Time	V _{DD} = -15 Vdc, I _D = -2.5 Adc,	t _r	-	9.7	-		
Turn-Off Delay Time	V_{DD} = -15 Vdc, I_D = -2.5 Adc, R_L = 50 Ω	t _{d(off)}	_	12	-		
Fall Time		t _f	_	1.7	-		
Gate Charge	$V_{DD} = -40 \text{ Vdc}, I_D = -0.5 \text{ A}, V_{GS} = -10 \text{ V}$	Q _T	-	2.2	_	nC	
SOURCE-DRAIN DIODE CHARA	ACTERISTICS						
Continuous Current		IS	-	-	-0.130	Α	
Pulsed Current	I _{SM}	-	-	-0.520			
Forward Voltage (Note 3)	$V_{GS} = 0 \text{ V}, I_{S} = -130 \text{ mA}$	V_{SD}	_	-	-2.2	V	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- 2. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
- 3. Switching characteristics are independent of operating junction temperature.

TYPICAL ELECTRICAL CHARACTERISTICS

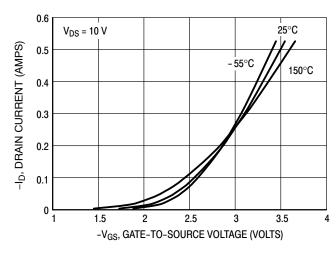


Figure 1. Transfer Characteristics

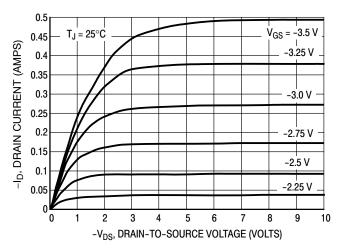


Figure 2. On-Region Characteristics

BSS84L, BVSS84L, SBSS84L

TYPICAL ELECTRICAL CHARACTERISTICS

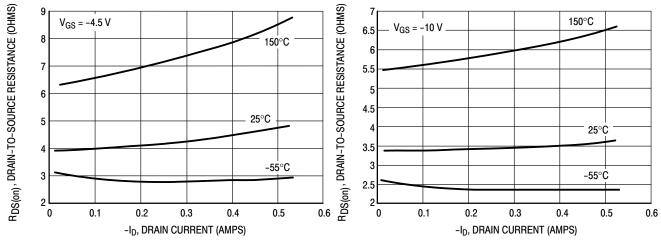


Figure 3. On-Resistance versus Drain Current

Figure 4. On-Resistance versus Drain Current

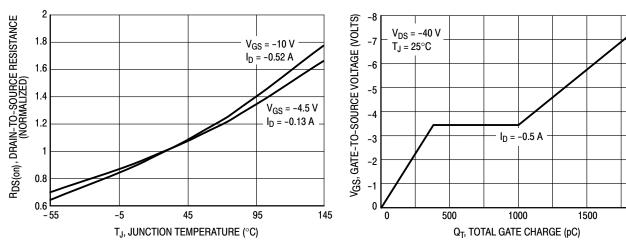


Figure 5. On-Resistance Variation with Temperature

Figure 6. Gate Charge

2000

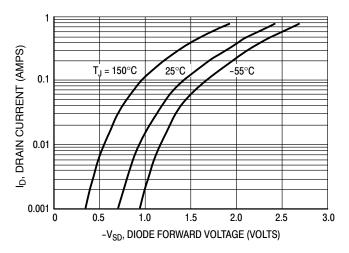


Figure 7. Body Diode Forward Voltage

MILLIMETERS

MIN

0.89

0.01

0.37

0.08

2.80

1.20

1.78

0.30

0.35

2.10

O°

NOM

1.00

0.06

0.44

0.14

2.90

1.30

1.90

0.43

0.54

2.40





SOT-23 (TO-236) 2.90x1.30x1.00 1.90P **CASE 318 ISSUE AU**

DATE 14 AUG 2024

MAX

1.11

0.10

0.50

0.20

3.04

1.40

2.04

0.55

0.69

2.64

10°

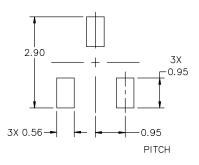




DETAIL "A" Scale 3:1







NOTES:

DIM

Α

Α1

b

С

D

Ε

е L

L1

HE

Τ

- DIMENSIONING AND TOLERANCING 1. PER ASME Y14.5M, 2018. CONTROLLING DIMENSIONS:
- MILLIMETERS.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE
- BASE MATERIAL.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code

= Date Code

= Pb-Free Package

RECOMMENDED MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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^{*}This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "=", may or may not be present. Some products may not follow the Generic Marking.

SOT-23 (TO-236) 2.90x1.30x1.00 1.90P CASE 318 ISSUE AU

DATE 14 AUG 2024

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR		NODE D CONNECTION ATHODE	
STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE	STYLE 11: STYLE 12: PIN 1. ANODE PIN 1. CA 2. CATHODE 2. CA 3. CATHODE-ANODE 3. AN	ATHODE PIN 1. SOURCE ATHODE 2. DRAIN	STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE	STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE			STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE
STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT	STYLE 23: STYLE 24: PIN 1. ANODE PIN 1. GAT 2. ANODE 2. DR/ 3. CATHODE 3. SOU	TE PIN 1. ANODE AIN 2. CATHODE	STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE			

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